

said step of plasma-etching conducted in a vacuum and in a process gas mixture comprising an inert gas, an oxygen gas, and a nitrogen gas ~~said process gas mixture and~~ further comprising a gas selected from the group consisting of a chlorine gas and a fluorine gas;

conducting the steps of forming a laminate, forming a protective layer, and plasma-etching
continuously; and

forming a lubricant layer on said first surface of said protective layer, whereby surface defects are minimized and surface quality is greatly improved.

Claim 17 (Cancelled)

Claim 18 (Original) A method according to claim 15 wherein:

said step of plasma-etching is conducted in a process gas mixture contain the process gas mixture of Ar, O₂, and N₂ where the mixing ratio thereof is substantially 6: 1: 3.

Claims 19-20 (Cancelled)